

Features

- Trench Power MV MOSFET Technology
- Very Low On-Resistance RDS(ON)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Moisture Sensitivity Level 1
- Halogen Free. "Green" Device (Note 1)
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

Maximum Ratings

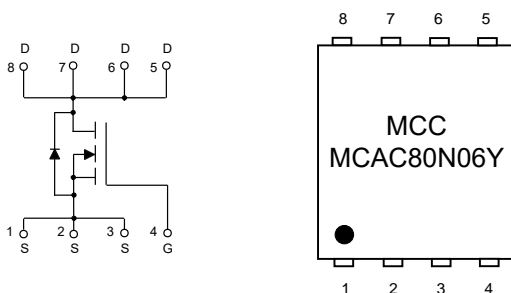
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 15°C/W Junction to Ambient(t≤10s)^(Note 2)
- Thermal Resistance: 43°C/W Junction to Ambient(Steady-State)^(Note2,3)
- Thermal Resistance: 1.47°C/W Junction to Case(Steady-State)

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V _{DS}	60	V
Gate-Source Voltage		V _{GS}	±20	V
Continuous Drain Current ^(Note 3)	T _C =25°C	I _D	80	A
	T _C =100°C		58	A
Pulsed Drain Current ^(Note 4)		I _{DM}	320	A
Single Pulse Avalanche Energy ^(Note 5)		E _{AS}	450	mJ
Total Power Dissipation ^(Note 2)	T _C =25°C	P _D	85	W
	T _C =100°C		34	W

Note:

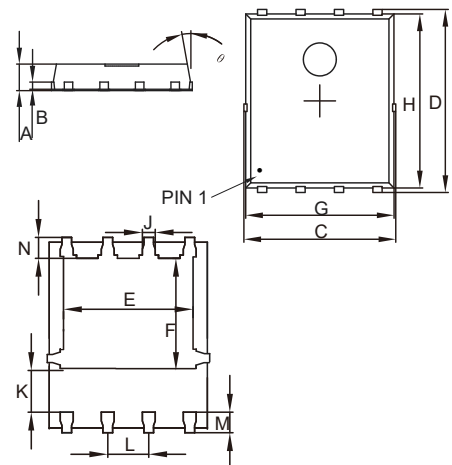
1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The Value of R_{θJA} is Measured with the Device Mounted on 1in² FR - 4 Board with 2oz. Copper, in a Still Air Environment with T_A=25°C. The Power Dissipation P_{DSM} is Based on R_{θJA} t≤10s and the Maximum Allowed Junction Temperature of 150°C. The Value in Any Given Application Depends on the User's Specific Board Design.
3. The R_{θJA} is the Sum of the Thermal Impedance from Junction to Case R_{θJC} and Case to Ambient.
4. The Maximum Current Rating is Package Limited.
5. Single Pulse Width Limited by Junction Temperature T_{J(MAX)}=175°C.

Internal Structure and Marking Code



N-CHANNEL MOSFET

DFN5060



DIM	DIMENSIONS				NOTE
	INCHES		MM		
	MIN	MAX	MIN	MAX	
A	0.031	0.047	0.80	1.20	
B	0.010		0.254		TYP.
C	0.193	0.222	4.90	5.64	
D	0.232	0.250	5.90	6.35	
E	0.148	0.167	3.75	4.25	
F	0.126	0.154	3.20	3.92	
G	0.189	0.213	4.80	5.40	
H	0.222	0.239	5.65	6.06	
K	0.045	0.059	1.15	1.50	
J	0.012	0.020	0.30	0.50	
L	0.046	0.054	1.17	1.37	
M	0.012	0.028	0.30	0.71	
N	0.016	0.028	0.40	0.71	

Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	60	65		V
Gate-Source Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$			1	μA
		$V_{DS}=60V, V_{GS}=0V, T_J=55^\circ C$			5	
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.1	1.7	2.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$		3.0	4.2	m Ω
		$V_{GS}=4.5V, I_D=20A$		3.9	5.2	
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=40A$	30			S
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=40A$		0.85	0.99	V
Continuous Body Diode Current	I_S				80	A
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS}=30V, V_{GS}=0V, f=1MHz$		3980		pF
Output Capacitance	C_{oss}			690		
Reverse Transfer Capacitance	C_{rss}			24		
Gate Resistance	R_g	$V_{DS}=0V, V_{GS}=0V, f=1MHz$		2.5		Ω
Switching Characteristics						
Total Gate Charge	Q_g	$V_{DS}=30V, V_{GS}=4.5V, I_D=40A$		32		nC
Total Gate Charge	Q_g	$V_{DS}=30V, V_{GS}=10V, I_D=40A$		67		
Gate-Source Charge	Q_{gs}			12		
Gate-Drain Charge	Q_{gd}			8.5		
Reverse Recovery Charge	Q_{rr}	$I_F=I_S, di/dt=500A/\mu s$		60		ns
Reverse Recovery Time	t_{rr}			48		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10V, V_{DS}=15V, R_L=2.5\Omega, R_{GEN}=3\Omega$		15		
Turn-On Rise Time	t_r			8		
Turn-Off Delay Time	$t_{d(off)}$			48		
Turn-Off Fall Time	t_f			12		

Curve Characteristics

Fig. 1 - Output Characteristics

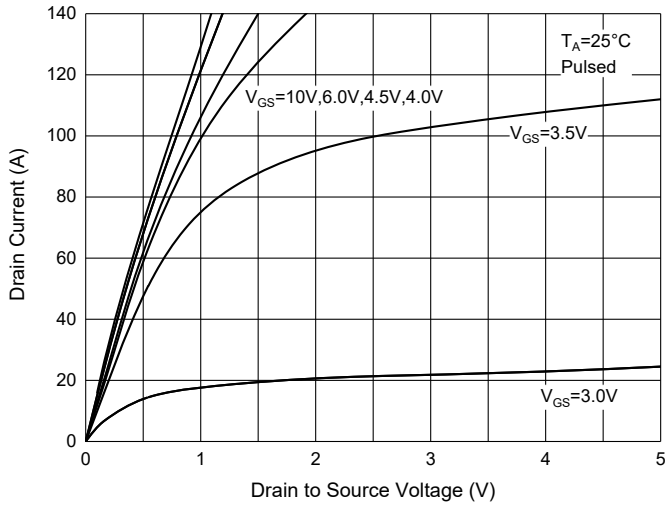


Fig. 2 - Transfer Characteristics

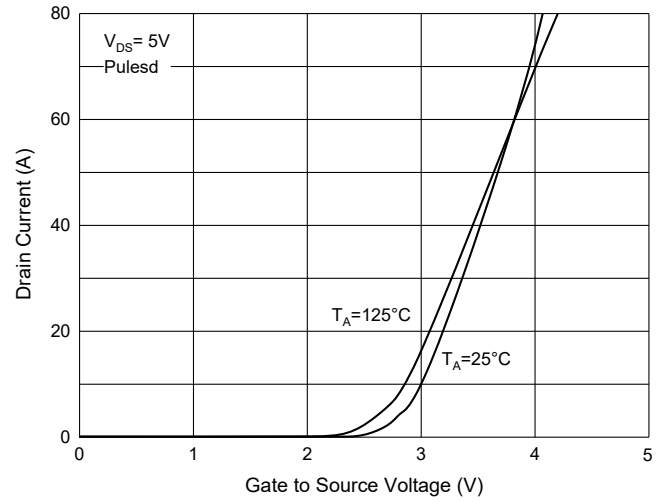


Fig. 3 - $R_{DS(ON)} - I_D$

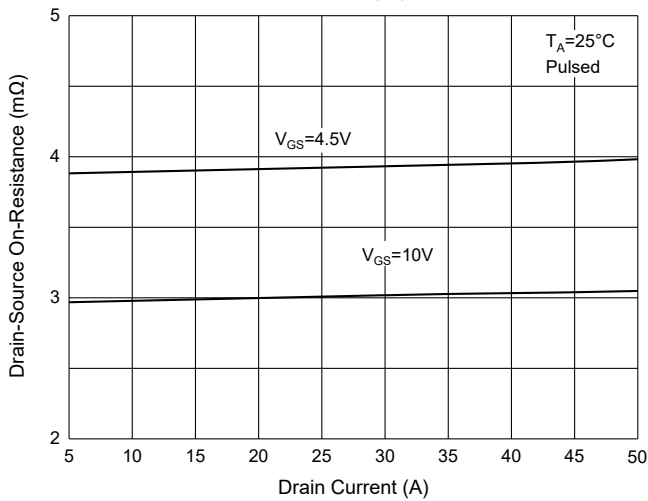


Fig. 4 - $I_S - V_{SD}$

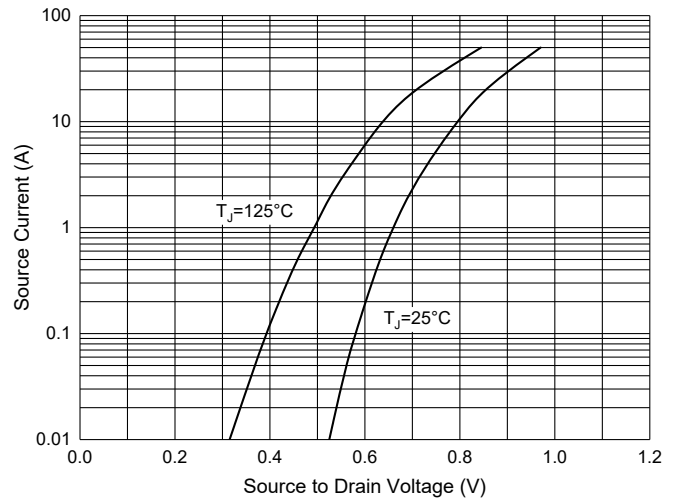


Fig. 5 - Gate Charge

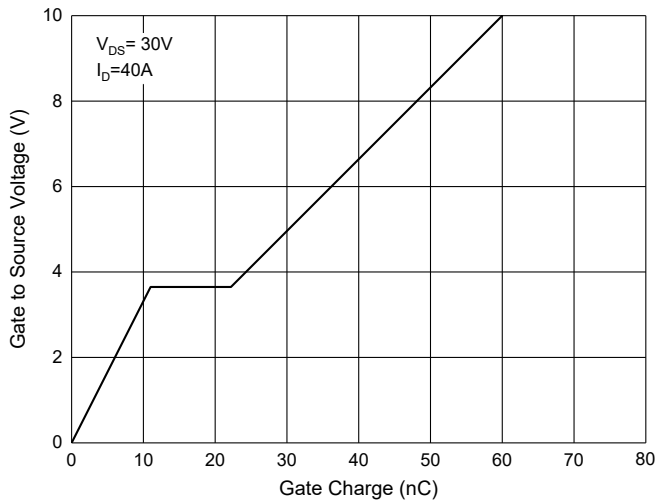
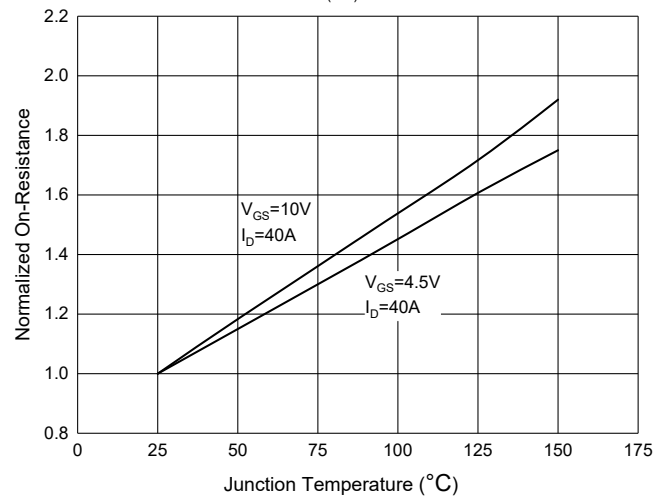


Fig. 6 - $R_{DS(ON)} - \text{Temperature}$



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 5Kpcs/Reel

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